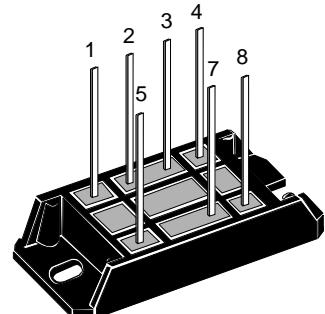
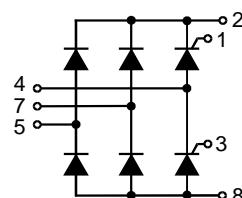


Three Phase Rectifier Bridge

V_{RRM} = 1600 V
I_{dAVM} = 43 A

V _{RSM}	V _{RRM}	Type
V _{DSM}	V _{DRM}	
V	V	
1700	1600	VVY 40-16io1



Symbol	Test Conditions	Maximum Ratings		
I _{dAV}	T _H = 100°C; module	34	A	
I _{dAVM}	module	43	A	
I _{FRMS} , I _{TRMS}	per leg	25	A	
I _{FSM} , I _{TSM}	T _{VJ} = 45°C; V _R = 0	320 350	A A	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
	T _{VJ} = T _{VJM} V _R = 0	290 320	A A	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
I ² dt	T _{VJ} = 45°C V _R = 0	510 520	A ² s A ² s	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
	T _{VJ} = T _{VJM} V _R = 0	420 430	A ² s A ² s	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 400 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 0.3 A, di _G /dt = 0.3 A/µs	150 500	A/µs A/µs	
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; V _{DR} = 2/3 V _{DRM} R _{GK} = ∞; method 1 (linear voltage rise)	1000	V/µs	
V _{RGM}	T _{VJ} = T _{VJM}	10	V	
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 µs t _p = 500 µs t _p = 10 ms	≤ 10 ≤ 5 ≤ 1	W W W
P _{GAVM}			0.5	W
T _{VJ}			-40...+125	°C
T _{VJM}			125	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~ V~
M _d	Mounting torque	(M5) (10-32 UNF)	2-2.5 18-22	Nm lb.in.
Weight	typ.		28	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Soldering terminals
- Separate thyristor for softstart
- UL registered E 72873

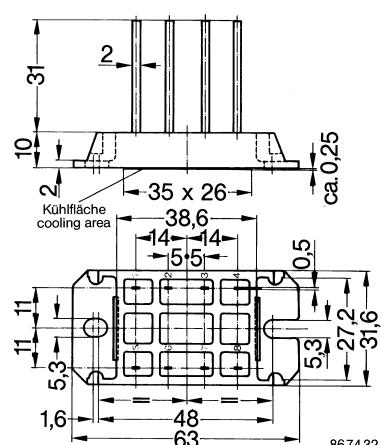
Applications

- Input rectifier for switch mode power supplies (SMPS)
- Softstart capacitor charging
- Electric drives and auxiliaries

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Values		
I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ C$	\leq	5	mA
		\leq	0.6	mA
V_F, V_T	$I_F, I_T = 30 A, T_{VJ} = 25^\circ C$	\leq	1.35	V
V_{TO} r_T	For power-loss calculations only $(T_{VJ} = 125^\circ C)$		0.85	V
			15	mΩ
V_{GT}	$V_D = 6 V;$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$	\leq	1.0	V
		\leq	1.2	V
I_{GT}	$V_D = 6 V;$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$ $T_{VJ} = 125^\circ C$	\leq	65	mA
		\leq	80	mA
		\leq	50	mA
V_{GD} I_{GD}	$T_{VJ} = T_{VJM};$ $V_D = \frac{2}{3} V_{DRM}$	\leq	0.2	V
	$T_{VJ} = T_{VJM};$ $V_D = \frac{2}{3} V_{DRM}$	\leq	5	mA
I_L	$I_G = 0.3 A; t_G = 30 \mu s$ $di_G/dt = 0.3 A/\mu s$	\leq	150	mA
	$T_{VJ} = 25^\circ C$	\leq	200	mA
	$T_{VJ} = -40^\circ C$	\leq	100	mA
$T_{VJ} = 125^\circ C$		\leq	100	mA
I_H	$T_{VJ} = 25^\circ C; V_D = 6 V; R_{GK} = \infty$	\leq	100	mA
t_{gd}	$T_{VJ} = 25^\circ C; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$	\leq	2	μs
t_q Q_r	$T_{VJ} = 125^\circ C; I_T = 15 A, t_p = 300 \mu s, -di/dt = 10 A/\mu s$ $V_R = 100 V, dv/dt = 20 V/\mu s, V_D = \frac{2}{3} V_{DRM}$		150	μs
			75	μC
R_{thJC}	per thyristor (diode); DC current		1.0	K/W
	per module		0.17	K/W
R_{thCH}	per thyristor (diode); DC current		0.6	K/W
d_s	Creeping distance on surface		7	mm
d_A	Creepage distance in air		7	mm
a	Max. allowable acceleration		50	m/s ²